

PH895DBR 895nm Series

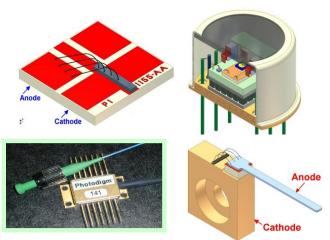
High-Power Single-Frequency Laser Diode

Technology

- DBR Single-Frequency Laser Chip
- InGaAs QW Active Layer
- Epi designed for high reliability

Features

- Available in several package styles
- Pulsed operation for spectral stability at short pulse lengths
- High power for CW applications
- High Slope Efficiency



Description

The PH895DBR Series of high-power edge-emitting lasers are based on Photodigm's advanced singlefrequency laser technology. It provides a diffraction limited, single lateral and longitudinal mode beam. Facets are passivated for high-power reliability. Devices used in atomic spectroscopy for cesium based applications.

Absolute Maximum Ratings

Parameter	Symbol	Unit	Min	Max
Storage Temperature	T _{STG}	С°	0	80
Operating Temperature	T _{OP}	С°	5.0	70
CW Laser Forward Current, T=T _{op}	I _F	mA	-	200**
Pulsed Laser Forward Current, T=25°C, PW=300 ns, DC=10%	I _F	А	-	0.5
Laser Reverse Voltage	V _R	V	-	0.0
Photodiode Forward Current 1/2/	I _P	mA	-	5.0
Photodiode Reverse Voltage 1/2/	V _R	V	-	20.0
Photodiode Dark Current, V _R =10V, LD I _F =0, 1/2/	I _D	nA	-	50
TEC Current 2/	I _{TEC}	A	-1.8	1.8
TEC Voltage 2/	V _{TEC}	V	-1.9	1.9
Thermistor Current 1/2/	I _{THRM}	mA	-	1.0
Thermistor Voltage 1/2/	V _{THRM}	V	-	10
ESD (HBM)	-	V	-	500
External Back Reflection	-	dB	-	-14
Lead Soldering Temperature, 10 sec. Max., 1/2/	-	С°	-	260
Fiber Pull Force <u>1</u> /	-	N	-	5.0
Fiber Bend Radius <u>1</u> /	-	mm	-	35

1/Butterfly package 2/TO-8 package** Do not exceed drive current or operating power of supplied LIV

Photodigm VVVAA

PRODUCT BULLETIN

CW Characteristics at T_C = 25°C unless otherwise specified

CW Characteristics at T _C = 25 C unless otherwise specified								
Parameter	Symbol	Unit	Min	Тур	Max			
Center Wavelength	λ _c	nm	893	895	897			
Optical Output Power @ LIV current	Po	mW	See Power Options Call-out					
Slope Efficiency, <u>1</u> /	η_{d}	W/A	0.3	0.36				
Slope Efficiency	η_{d}	W/A	0.6	0.72	-			
Threshold Current	l _{th}	mA	-	40	50			
Laser Series Resistance	Rs	Ω	-	2.5	3.5			
Laser Forward Voltage	V _F	V	-	2.0	2.5			
Thermistor Resistance @ 25°C, <u>1/2</u> /	R _T	KΩ	-	10	-			
Photodiode Dark Current, V _R =10V, LD I _F =0, <u>1/2</u> /	I _D	nA	-	-	50			
Laser Line Width	Δv	MHz	-	0.5	1			
Beam Divergence @ FWHM	Өн Х Ө⊥	0	-	6 X 32	8 X 34			
Side Mode Suppression Ratio	SMSR	dB	-30	-	-			
Polarization Extinction Ratio, 1/	PER	dB	-16	-19	-			
Laser Polarization				TE				
Mode Structure			Fundamental Mode					
			•					

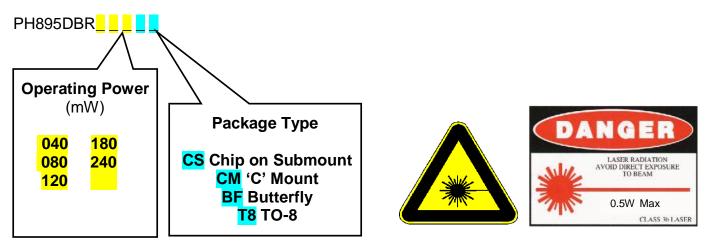
1/Butterfly package 2/TO-8 package

Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic container with all leads shorted together.

How To Order

Part number example: PH895DBR080CM. Assign optical power from those shown below. Use a three-digit format for all power entries. Call factory for special performance selection and certification to certain atomic absorption lines. Butterfly package offered with 40mW operating power only and is not recommended for spectroscopy applications. See Photodigm's application note titled "Optical Feedback"



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